

Low-Voltage Quad 2-Input AND Gate with 5V Tolerant Inputs and Outputs

The TC74LCX08 is a high performance CMOS 2-INPUT AND GATE. Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

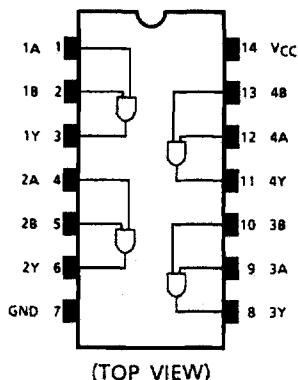
The device is designed for low voltage (3.3V) V_{CC} applications, but it could be used to interface to 5V supply environment for inputs.

All inputs are equipped with protection circuits against static discharge.

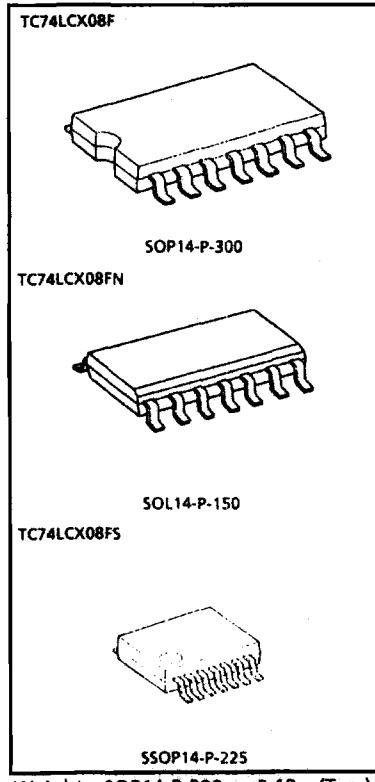
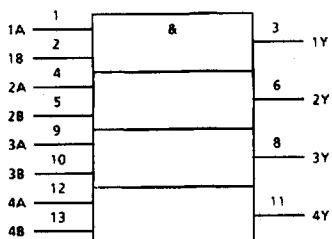
Features

- Low Voltage Operation: $V_{CC} = 2.0 \sim 3.6V$
- High Speed: $t_{pd} = 5.5ns$ (Max.) at $V_{CC} = 3.0 \sim 3.6V$
- Output Current: $I_{O_H}/I_{O_L} = 24mA$ (Min.) $V_{CC} = 3.0V$
- Latch up Performance: $\pm 500mA$
- Available in JEDEC SOP, EIAJ SOP and SSOP
- Power down protection is provided on all inputs and outputs
- Pin and Function Compatible with 74 series
 - (74AC/VHC/HC/F/ALS/LS, etc.) 08 type

Pin Connection



IEC Logic Symbol



Weight SOP14-P-300 : 0.18g (Typ.)
 SOL14-P-150 : 0.12g (Typ.)
 SSOP14-P-225 : 0.07g (Typ.)

Pin Assignment

Truth Table

Inputs		Outputs
A	B	Y
L	L	L
L	H	L
H	L	L
H	H	H

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply Voltage Range	V _{CC}	-0.5 ~ 7.0	V
DC Input Voltage	V _{IN}	-0.5 ~ 7.0	V
DC Output Voltage	V _{OUT}	-0.5 ~ 7.0 (Note 1)	V
		-0.5 ~ V _{CC} + 0.5 (Note 2)	
Input Diode Current	I _{IK}	-50	mA
Output Diode Current	I _{OK}	±50 (Note 3)	mA
DC Output Current	I _{OUT}	±50	mA
Power Dissipation	P _D	180	mW
DC V _{CC} /Ground Current	I _{CC/GND}	±100	mA
Storage Temperature	T _{STG}	-65 ~ 150	°C

(Note 1) Off-State

(Note 2) High or Low State. I_{OUT} absolute maximum rating must be observed.(Note 3) V_{OUT} < GND, V_{OUT} > V_{CC}**Recommended Operating Conditions**

Parameter	Symbol	Value	Unit
Supply Voltage	V _{CC}	2.0 ~ 3.6	V
		1.5 ~ 3.6 (Note 4)	
Input Voltage	V _{IN}	0 ~ 5.5	V
Bus Output Voltage	V _{OUT}	0 ~ 5.5 (Note 5)	V
		0 ~ V _{CC} (Note 6)	
Output Current	I _{OH/I_{OL}}	±24 (Note 7)	mA
		±12 (Note 8)	
Operating Temperature	T _{opr}	-40 ~ 85	°C
Input Rise and Fall Time	d _{t/dv}	0 ~ 10 (Note 9)	ns/V

(Note 4) Data Retention Only

(Note 5) Off-State

(Note 6) High or Low State

(Note 7) V_{CC} = 3.0 ~ 3.6V(Note 8) V_{CC} = 2.7 ~ 3.0V(Note 9) V_{IN} = 0.8 ~ 2.0V, V_{CC} = 3.0V**Electrical Characteristics****DC Characteristics (Ta = -40 ~ 85°C)**

Parameter	Symbol	Test Condition	V _{CC} (M)	Min.	Max.	Unit
				Min.	Max.	
Input Voltage	V _{IH}	—	2.7 ~ 3.6	2.0	—	V
	V _{IL}	—	2.7 ~ 3.6	—	0.8	V
Output Voltage	V _{OH}	V _{IN} = V _{IH}	I _{OH} = -100µA I _{OH} = -12mA I _{OH} = -18mA I _{OH} = -24mA	2.7 ~ 3.6 2.7 3.0 3.0	V _{CC} = 0.2 2.2 2.4 2.2	V
	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = 100µA I _{OL} = 12mA I _{OL} = 16mA I _{OH} = 24mA	2.7 ~ 3.6 2.7 3.0 3.0	— — — —	V
Input Leakage Current	I _{IN}	V _{IN} = 0 ~ 5.5V	2.7 ~ 3.6	—	±5.0	µA
Power Off Leakage Current	I _{OFF}	V _{IN} /V _{OUT} = 5.5V	0	—	10.0	µA
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND	2.7 ~ 3.6	—	10.0	µA
		V _{IN} /V _{OUT} = 3.6 ~ 5.5V	2.7 ~ 3.6	—	±10.0	
Increase in I _{CC} per Input	ΔI _{CC}	V _{IH} = V _{CC} - 0.6V	2.7 ~ 3.6	—	500	µA

AC Characteristics (Ta = -40 ~ 85°C)

Parameter	Symbol	Test Condition	V _{CC} (V)	Min.	Max.	Unit
Propagation Delay Time	t _{pLH}	(Fig. 1, 2)	2.7	—	6.2	ns
	t _{pHL}		3.3 ± 0.3	1.5	5.5	
Output to Output Skew	t _{osLH}	(Note 10)	2.7	—	—	ns
	t _{osHL}		3.3 ± 0.3	—	1.0	

(Note 10) Parameter guaranteed by design. t_{osLH} = (|t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)

Dynamic Switching Characteristics (Ta = 25°C, Input t_r = t_f = 2.5ns, C_L = 50pF, R_L = 500Ω)

Parameter	Symbol	Test Condition	V _{CC} (V)	Typical	Unit
Quiet Output Maximum Dynamic V _{OL}	V _{OLP}	V _{IH} = 3.3V, V _{IL} = 0V	3.3	0.8	V
Quiet Output Minimum Dynamic V _{OL}	V _{OLV}	V _{IH} = 3.3V, V _{IL} = 0V	3.3	0.8	V

Capacitive Characteristics (Ta = 25°C)

Parameter	Symbol	Test Condition	V _{CC} (V)	Typical	Unit
Input Capacitance	C _{IN}	—	3.3	7	pF
Bus Input Capacitance	C _{OUT}	—	3.3	8	pF
Power Dissipation Capacitance	C _{PD}	f _{IN} = 10MHz (Note 11)	3.3	25	pF

(Note 11) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation: I_{CC} (opr.) = C_{PD} • V_{CC} • f_{IN} + I_{CC}/4 (per gate)

TEST CIRCUIT

Fig.1

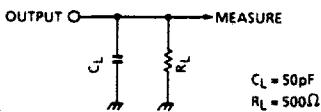
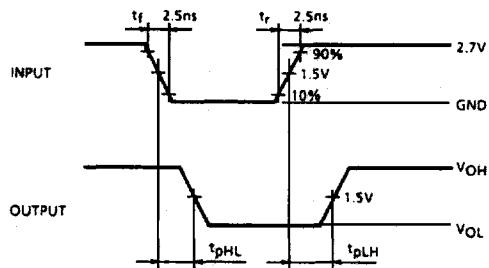
**AC WAVEFORM**

Fig.2 tpLH, tpHL



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